

# 2SH17

## Silicon N-Channel IGBT

# HITACHI

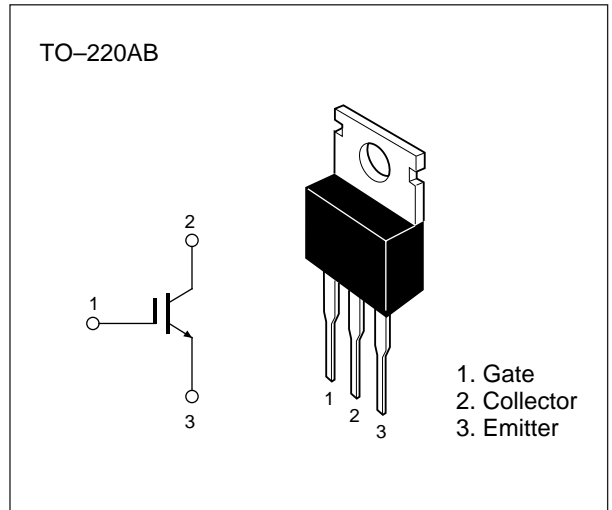
1st. Edition  
Feb. 1995

### Application

High speed power switching

### Features

- High speed switching
- Low on saturation voltage



**Table 1 Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

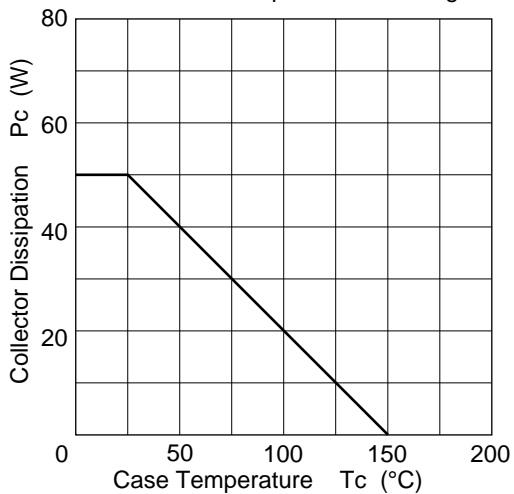
Item	Symbol	Ratings	Unit
Collector to emitter voltage	$V_{CES}$	600	V
Gate to emitter voltage	$V_{GES}$	$\pm 20$	V
Collector current	$I_C$	12	A
Collector peak current	$i_{c(\text{peak})}$	20	A
Collector dissipation	$P_C^*$	50	W
Channel temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\* Value at  $T_c = 25^\circ\text{C}$

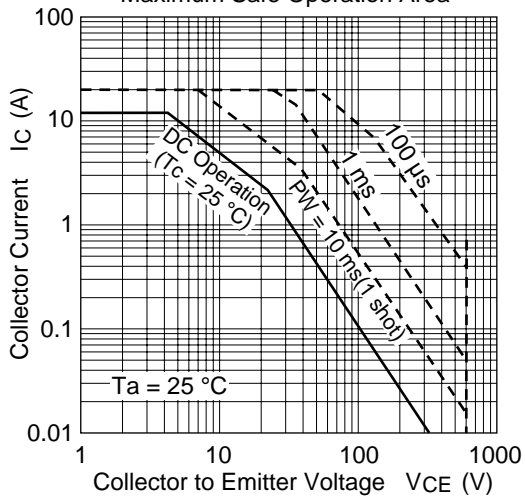
**Table 2 Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CES}$	600	—	—	V	$I_C = 100 \mu\text{A}, V_{GE} = 0$
Zero gate voltage collector current	$I_{CES}$	—	—	0.5	mA	$V_{CE} = 600 \text{ V}, V_{GE} = 0$
Gate to emitter leak current	$I_{GES}$	—	—	$\pm 1$	$\mu\text{A}$	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff current	$V_{GE(off)}$	3.0	—	6.0	V	$I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	1.5	—	V	$I_C = 5 \text{ A}, V_{GE} = 15 \text{ V}$
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	2.0	2.6	V	$I_C = 10 \text{ A}, V_{GE} = 15 \text{ V}$
Input capacitance	$C_{ies}$	—	1000	—	pF	$V_{CE} = 10 \text{ V}, V_{GE} = 0,$ $f = 1 \text{ MHz}$
Switching time	$t_r$	—	75	—	ns	$I_C = 10 \text{ A},$ $R_L = 30 \Omega,$ $V_{GE} = \pm 15 \text{ V}$ $R_g = 50 \Omega$
	$t_{on}$	—	150	—		
	$t_f$	—	2000	—		
	$t_{off}$	—	2300	—		

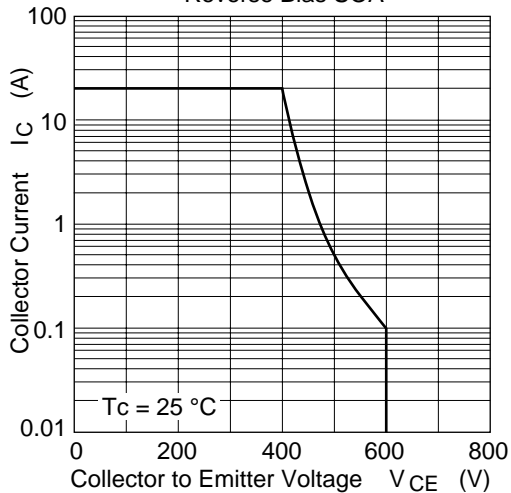
Power vs. Temperature Derating



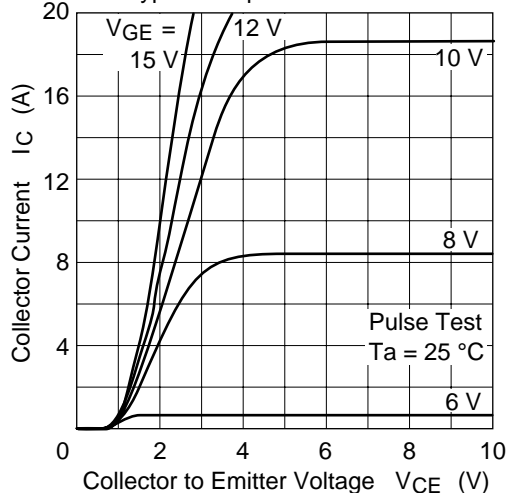
Maximum Safe Operation Area

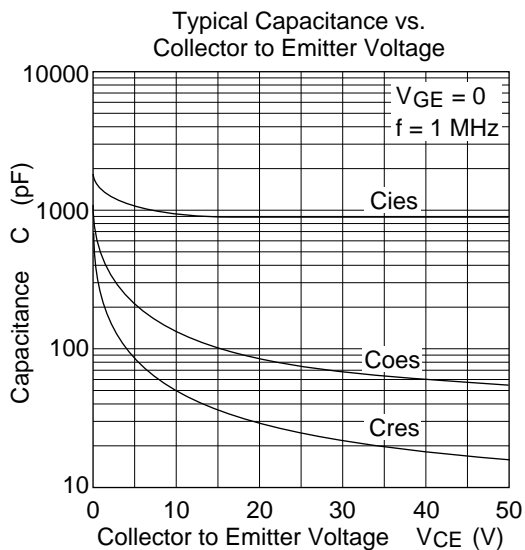
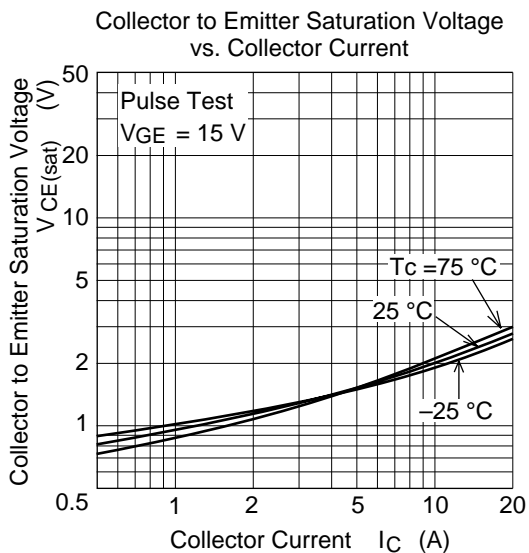
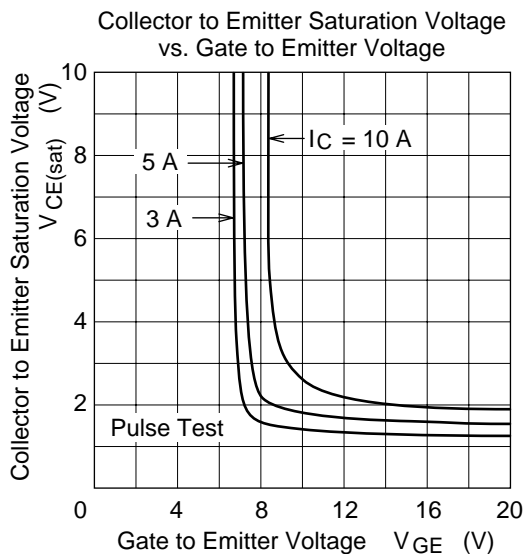
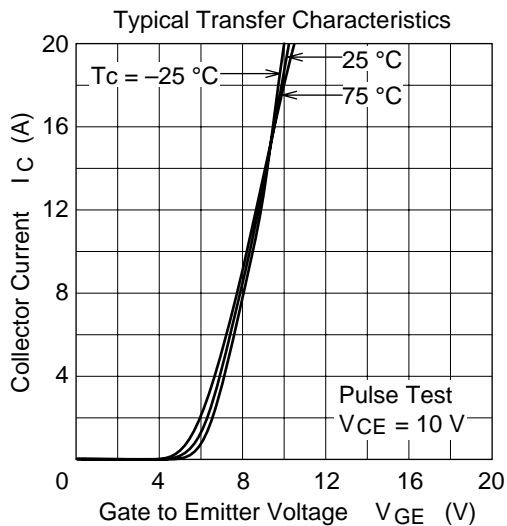


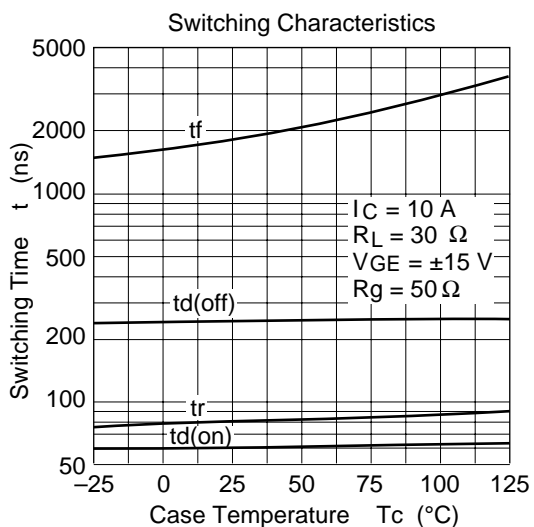
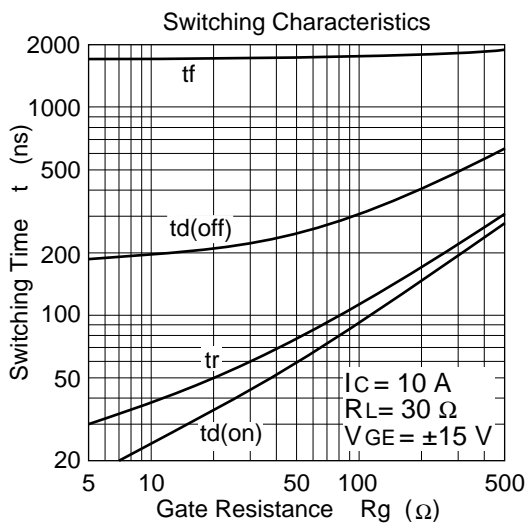
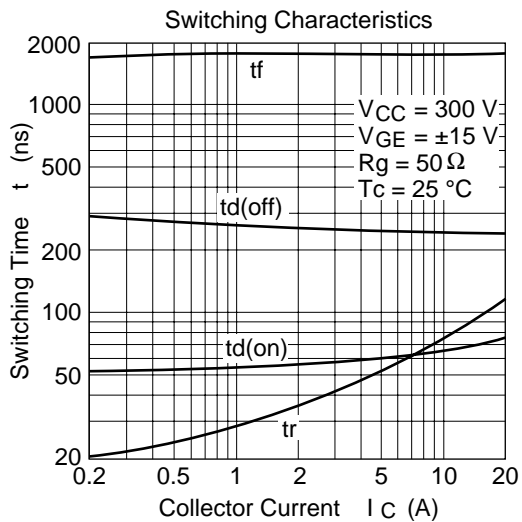
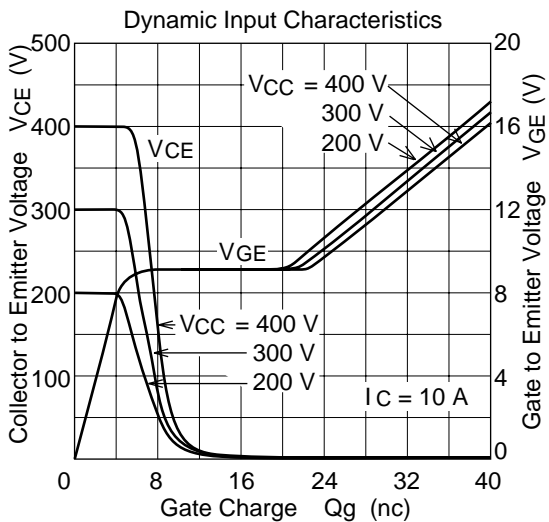
Reverse Bias SOA

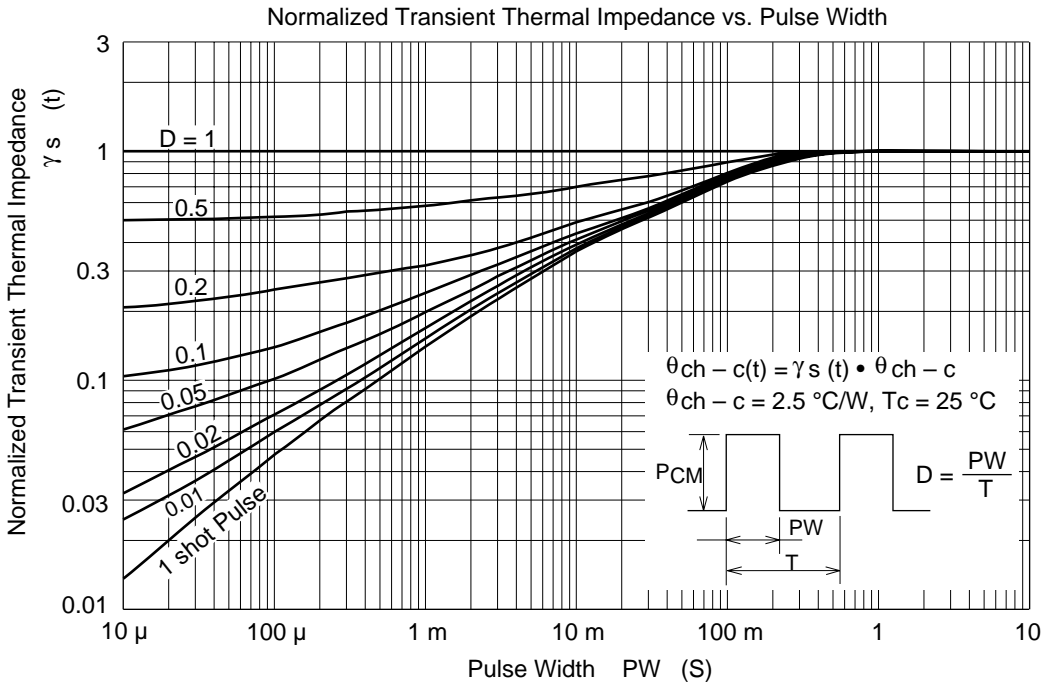


Typical Output Characteristics





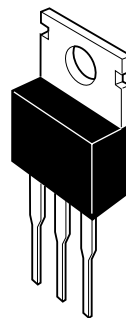
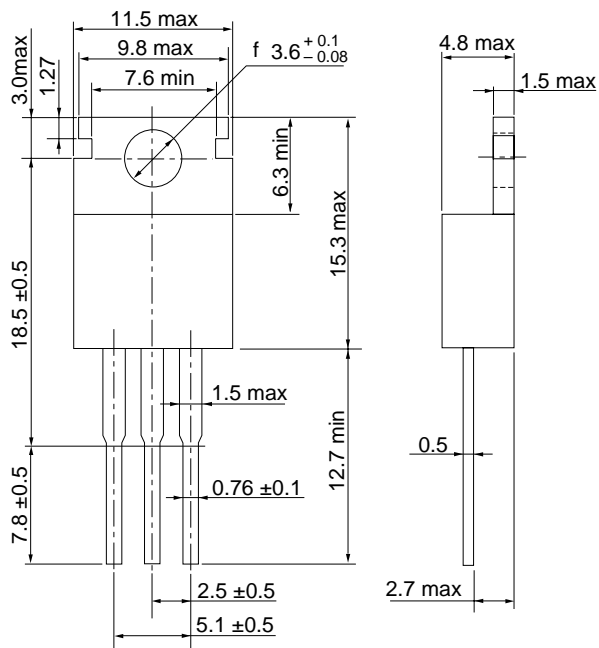




## Package Dimensions

Unit : mm

## • TO-220AB



Hitachi Code	TO-220AB
EIAJ	SC-46
JEDEC	—

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